

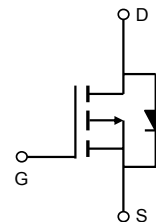
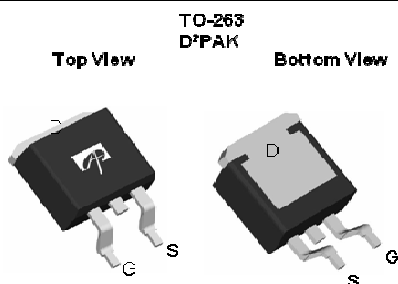
General Description

The AOB411L combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$. This device is ideal for boost converters and synchronous rectifiers for consumer, telecom, industrial power supplies and LED backlighting.

Product Summary

| | |
|-----------------------------------|------------------|
| V_{DS} | -60V |
| I_D (at $V_{GS}=-10V$) | -78A |
| $R_{DS(ON)}$ (at $V_{GS}=-10V$) | < 16.5m Ω |
| $R_{DS(ON)}$ (at $V_{GS}=-4.5V$) | < 22m Ω |

100% UIS Tested
 100% R_g Tested



Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

| Parameter | Symbol | Maximum | Units |
|--|------------------|-------------------------|------------------|
| Drain-Source Voltage | V_{DS} | -60 | V |
| Gate-Source Voltage | V_{GS} | ± 20 | V |
| Continuous Drain Current | I_D | $T_C=25^\circ\text{C}$ | -78 |
| | | $T_C=100^\circ\text{C}$ | -55 |
| Pulsed Drain Current ^C | I_{DM} | -230 | A |
| Continuous Drain Current | I_{DSM} | $T_A=25^\circ\text{C}$ | -8 |
| | | $T_A=70^\circ\text{C}$ | -6.5 |
| Avalanche Current ^C | I_{AS}, I_{AR} | -77 | A |
| Avalanche energy $L=0.1\text{mH}$ ^C | E_{AS}, E_{AR} | 296 | mJ |
| Power Dissipation ^B | P_D | $T_C=25^\circ\text{C}$ | 187 |
| | | $T_C=100^\circ\text{C}$ | 93 |
| Power Dissipation ^A | P_{DSM} | $T_A=25^\circ\text{C}$ | 2.1 |
| | | $T_A=70^\circ\text{C}$ | 1.3 |
| Junction and Storage Temperature Range | T_J, T_{STG} | -55 to 175 | $^\circ\text{C}$ |

Thermal Characteristics

| Parameter | Symbol | Typ | Max | Units |
|--|-----------------|--------------|-----|---------------------------|
| Maximum Junction-to-Ambient ^A | $R_{\theta JA}$ | 11 | 15 | $^\circ\text{C}/\text{W}$ |
| Maximum Junction-to-Ambient ^{A D} | | Steady-State | 47 | 60 |
| Maximum Junction-to-Case | $R_{\theta JC}$ | 0.6 | 0.8 | $^\circ\text{C}/\text{W}$ |

Electrical Characteristics (T_J=25°C unless otherwise noted)

| Symbol | Parameter | Conditions | Min | Typ | Max | Units |
|-----------------------------|--|---|------|--------------|------------|-------|
| STATIC PARAMETERS | | | | | | |
| BV _{DSS} | Drain-Source Breakdown Voltage | I _D =-250μA, V _{GS} =0V | -60 | | | V |
| I _{DSS} | Zero Gate Voltage Drain Current | V _{DS} =-60V, V _{GS} =0V T _J =55°C | | | -1 -5 | μA |
| I _{GSS} | Gate-Body leakage current | V _{DS} =0V, V _{GS} = ±20V | | | ±100 | nA |
| V _{GS(th)} | Gate Threshold Voltage | V _{DS} =V _{GS} , I _D =-250μA | -1.5 | -2 | -2.5 | V |
| I _{D(ON)} | On state drain current | V _{GS} =-10V, V _{DS} =-5V | -230 | | | A |
| R _{DS(ON)} | Static Drain-Source On-Resistance | V _{GS} =-10V, I _D =-20A T _J =125°C | | 13.5 20.5 | 16.5 25 | mΩ |
| | | V _{GS} =-4.5V, I _D =-20A | | 17 | 22 | mΩ |
| g _{FS} | Forward Transconductance | V _{DS} =-5V, I _D =-20A | | 48 | | S |
| V _{SD} | Diode Forward Voltage | I _S =-1A, V _{GS} =0V | | -0.7 | -1 | V |
| I _S | Maximum Body-Diode Continuous Current ^G | | | | -105 | A |
| DYNAMIC PARAMETERS | | | | | | |
| C _{iss} | Input Capacitance | V _{GS} =0V, V _{DS} =-30V, f=1MHz | 4260 | 5330 | 6400 | pF |
| C _{oss} | Output Capacitance | | 335 | 483 | 630 | pF |
| C _{riss} | Reverse Transfer Capacitance | | 140 | 234 | 330 | pF |
| R _g | Gate resistance | V _{GS} =0V, V _{DS} =0V, f=1MHz | 1.4 | 2.8 | 4.2 | Ω |
| SWITCHING PARAMETERS | | | | | | |
| Q _g (10V) | Total Gate Charge | V _{GS} =-10V, V _{DS} =-30V, I _D =-20A | 65 | 83 | 100 | nC |
| Q _g (4.5V) | Total Gate Charge | | 35 | 40 | 50 | nC |
| Q _{gs} | Gate Source Charge | | | 15 | | nC |
| Q _{gd} | Gate Drain Charge | | | 18 | | nC |
| t _{D(on)} | Turn-On DelayTime | V _{GS} =-10V, V _{DS} =-30V, R _L =1.5Ω, R _{GEN} =3Ω | | 17.5 | | ns |
| t _r | Turn-On Rise Time | | | 20 | | ns |
| t _{D(off)} | Turn-Off DelayTime | | | 83.5 | | ns |
| t _f | Turn-Off Fall Time | | | 37 | | ns |
| t _{rr} | Body Diode Reverse Recovery Time | I _F =-20A, dI/dt=500A/μs | 18 | 27 | 36 | ns |
| Q _{rr} | Body Diode Reverse Recovery Charge | I _F =-20A, dI/dt=500A/μs | 110 | 165 | 215 | nC |

A. The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The Power dissipation P_{DSM} is based on R_{θJA} and the maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design, and the maximum temperature of 175°C may be used if the PCB allows it.

B. The power dissipation P_D is based on T_{J(MAX)}=175°C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=175°C. Ratings are based on low frequency and duty cycles to keep initial T_J=25°C.

D. The R_{θJA} is the sum of the thermal impedance from junction to case R_{θJC} and case to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300μs pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T_{J(MAX)}=175°C. The SOA curve provides a single pulse rating.

G. The maximum current limited by package.

H. These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

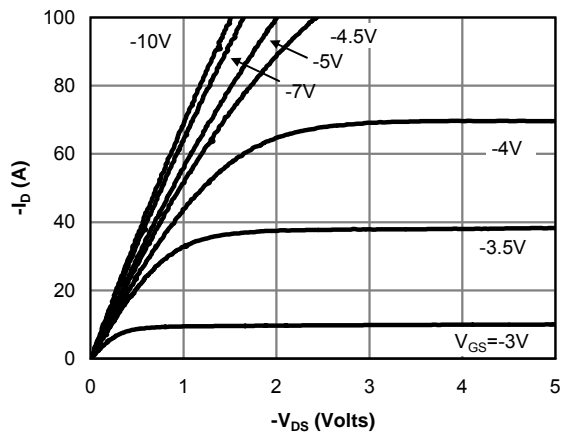


Fig 1: On-Region Characteristics (Note E)

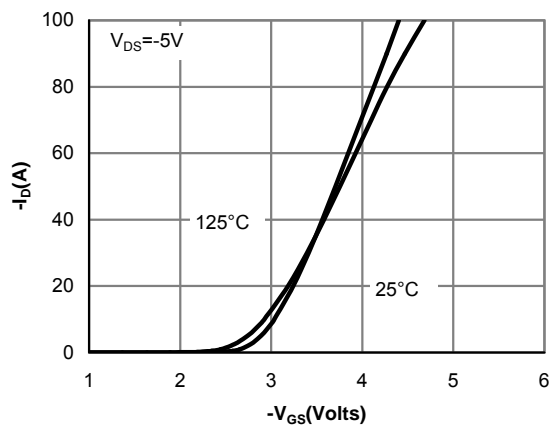


Figure 2: Transfer Characteristics (Note E)

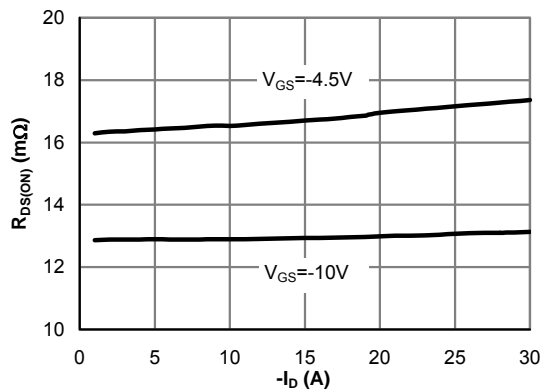


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

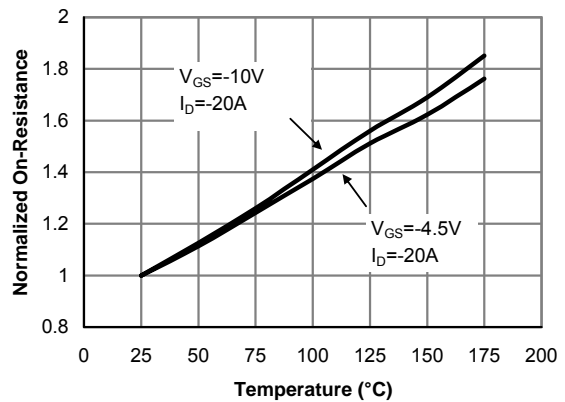


Figure 4: On-Resistance vs. Junction Temperature (Note E)

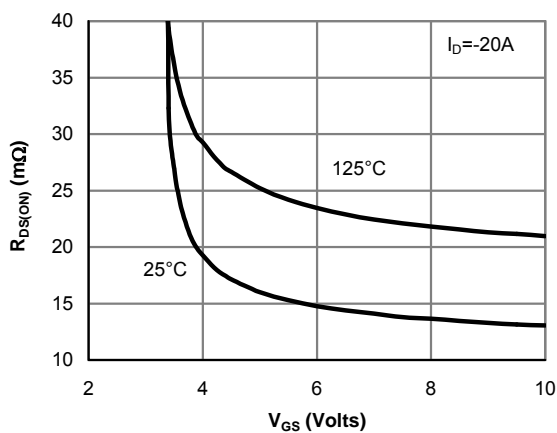


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

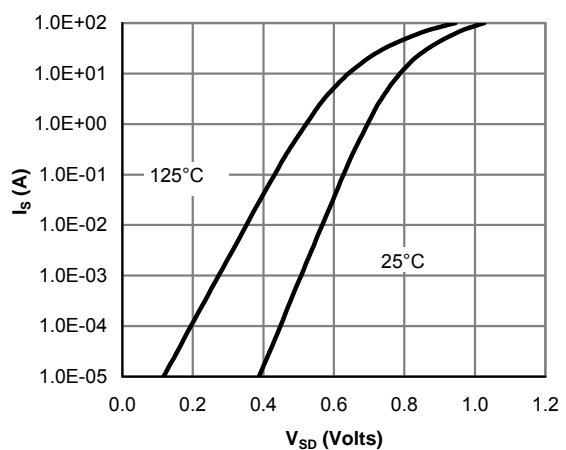


Figure 6: Body-Diode Characteristics (Note E)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

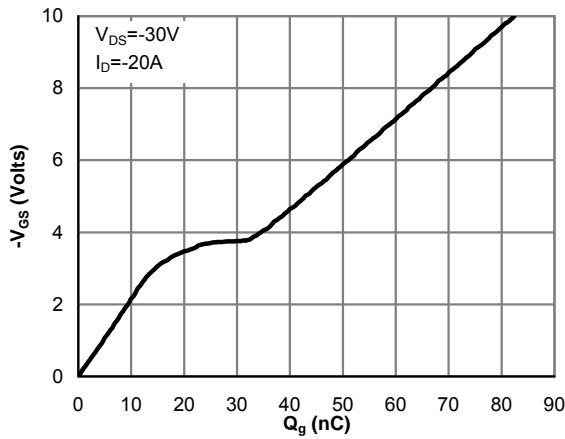


Figure 7: Gate-Charge Characteristics

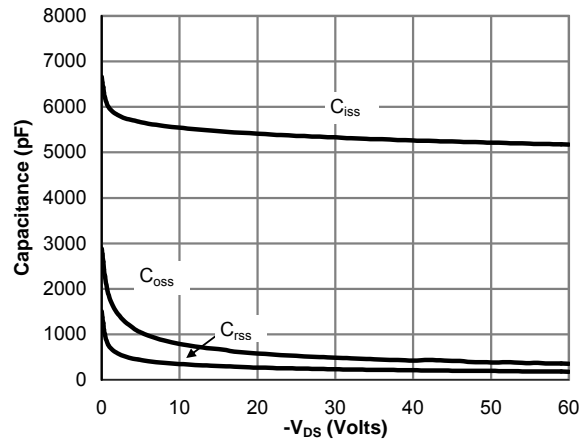


Figure 8: Capacitance Characteristics

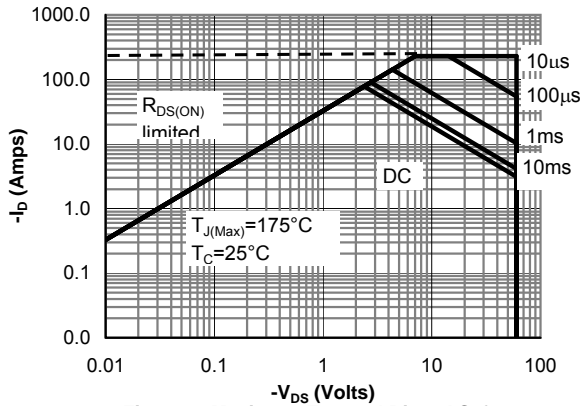


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

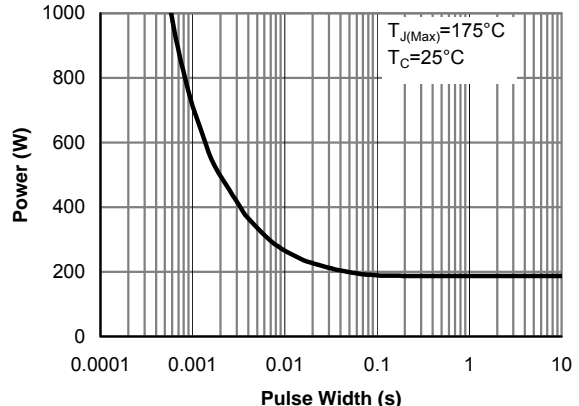


Figure 10: Single Pulse Power Rating Junction-to-Case (Note F)

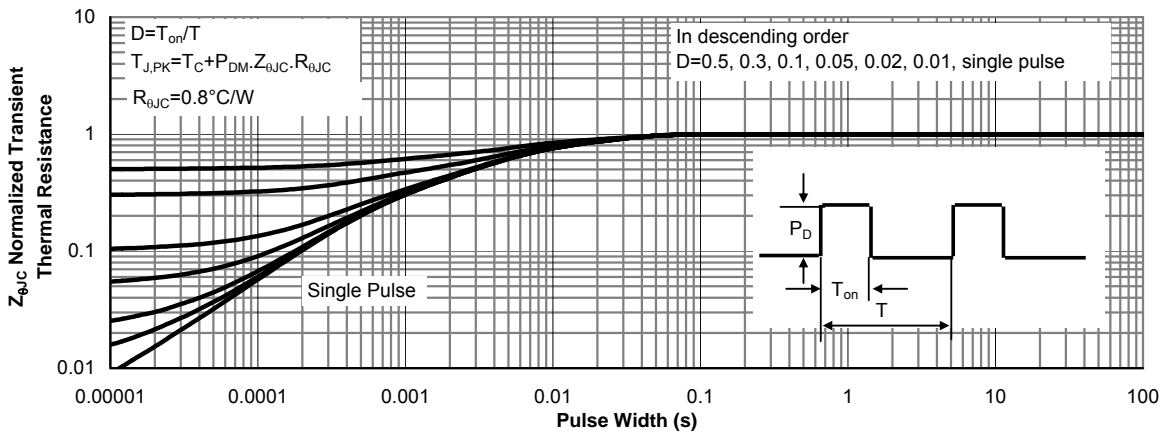


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

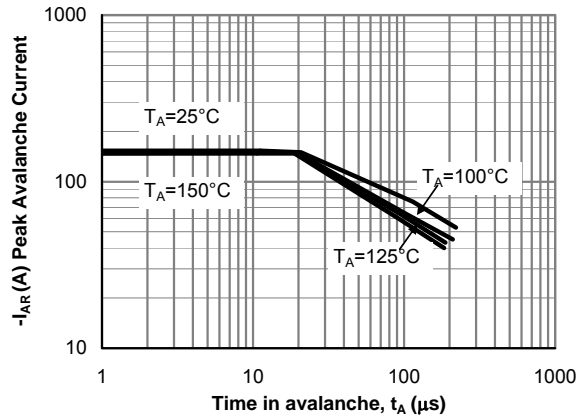


Figure 12: Single Pulse Avalanche capability (Note C)

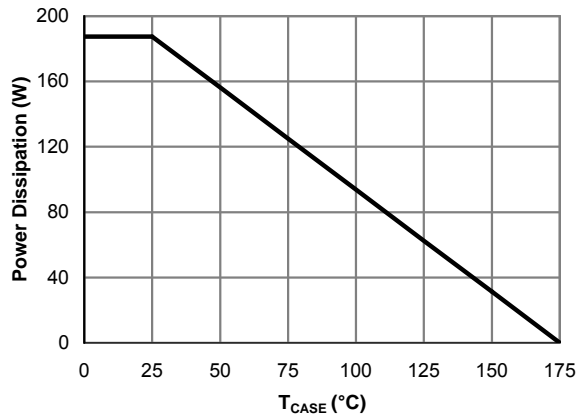


Figure 13: Power De-rating (Note F)

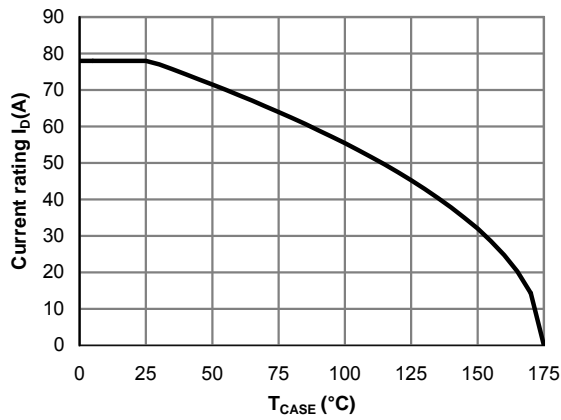


Figure 14: Current De-rating (Note F)

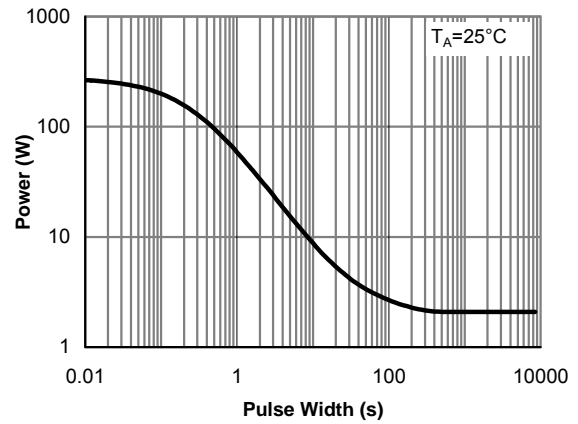


Figure 15: Single Pulse Power Rating Junction-to-Ambient (Note H)

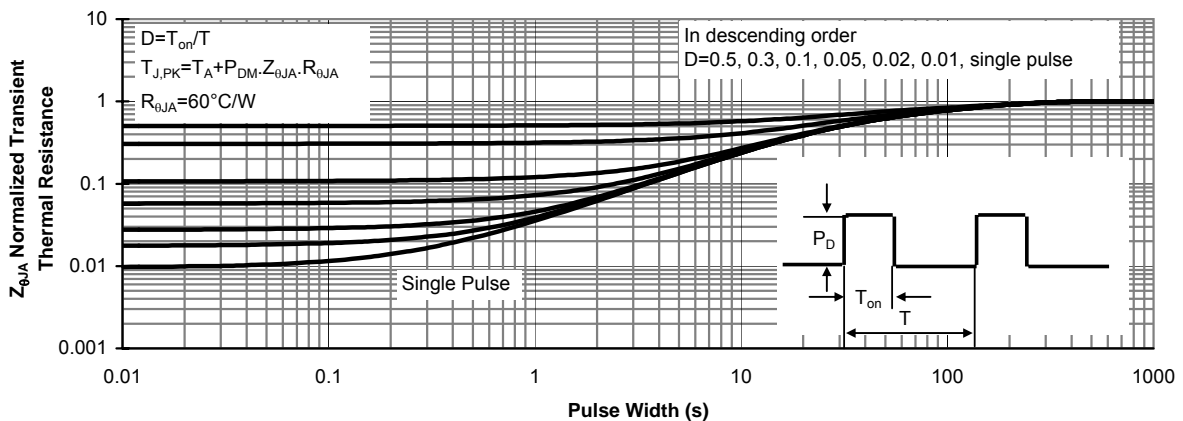
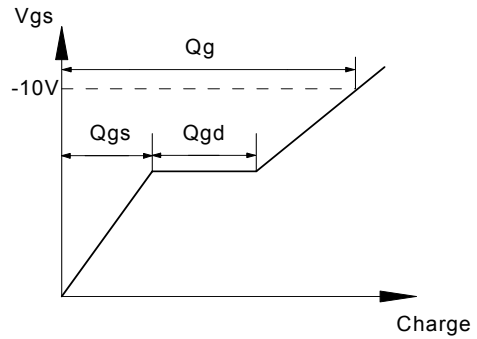
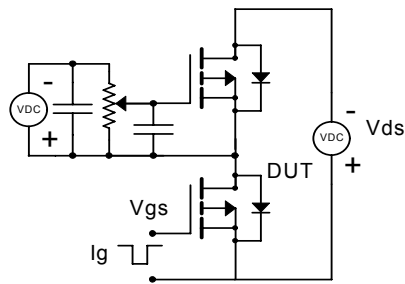
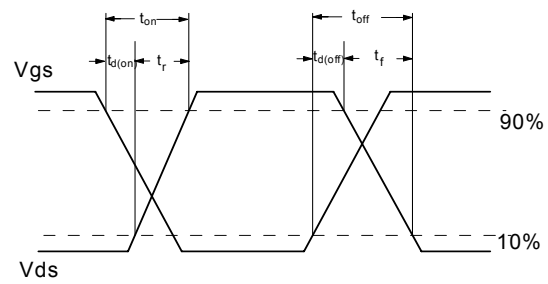
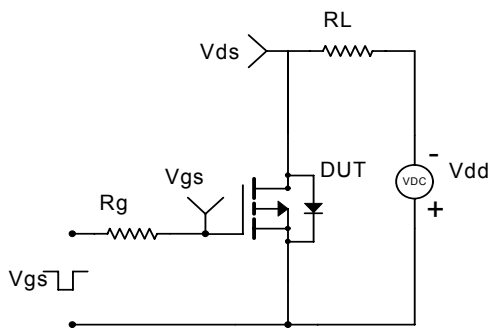


Figure 16: Normalized Maximum Transient Thermal Impedance (Note H)

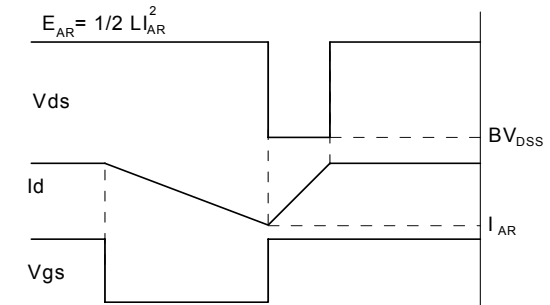
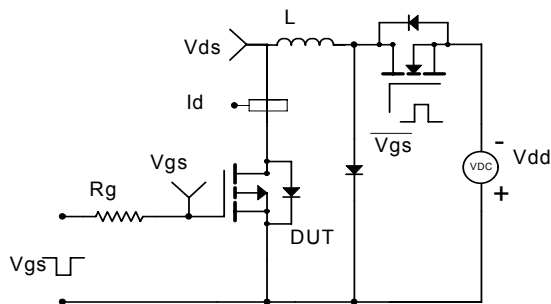
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms

